Title (en)

PROCESS FOR THE REMOVAL OF SILICON DIOXIDE RESIDUE FROM A SEMICONDUCTOR SURFACE

Publication

EP 0000701 B1 19810916 (DE)

Application

EP 78100336 A 19780710

Priority

US 82438277 A 19770815

Abstract (en)

[origin: US4116714A] Semiconductor materials are cleaned after silica polishing by treatment with an aqueous phosphoric acid containing solution followed by rinsing in water. The treatment dissolves the silica sols so that they are removed from the semiconductor surface.

IPC 1-7

H01L 21/302; C09K 13/04

IPC 8 full level

H01L 21/308 (2006.01); **C23G 1/00** (2006.01); **H01L 21/304** (2006.01); **H01L 21/306** (2006.01)

CPC (source: EP US)

C23G 1/00 (2013.01 - EP US); **H01L 21/02052** (2013.01 - EP US)

Designated contracting state (EPC)

DE FR GB

DOCDB simple family (publication)

US 4116714 A 19780926; DE 2861075 D1 19811203; EP 0000701 A2 19790221; EP 0000701 A3 19790307; EP 0000701 B1 19810916; JP S5432262 A 19790309; JP S6214938 B2 19870404

DOCDB simple family (application)

US 82438277 A 19770815; DE 2861075 T 19780710; EP 78100336 A 19780710; JP 8410178 A 19780712